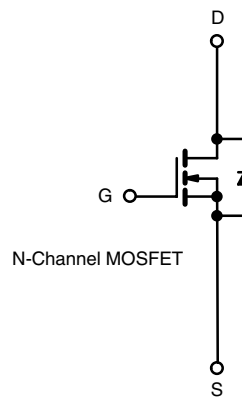
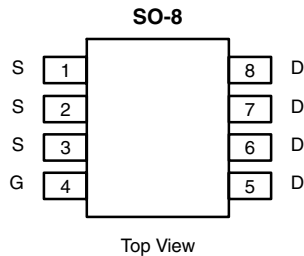


N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.012 @ $V_{GS} = 10$ V	12.4
	0.020 @ $V_{GS} = 4.5$ V	9.6

FEATURES

- TrenchFET® Power MOSFET
- High Efficiency PWM Optimized
- 100% R_g Tested
- 100% UIS Tested



Ordering Information: Si4892DY-T1
Si4892DY-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	12.4	8.8	A
	$T_A = 70^\circ\text{C}$		9.9	7.0	
Pulsed Drain Current		I_{DM}	± 50		
Continuous Source Current (Diode Conduction) ^a		I_S	2.60	1.3	
Avalanche Current	L = 0.1 mH	I_{AS}	20		
Single-Pulse Avalanche Energy		E_{AS}	20		mJ
Maximum Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	3.1	1.6	W
	$T_A = 70^\circ\text{C}$		2.0	1.0	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		$^\circ\text{C}$

THERMAL RATINGS RESISTANCE					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET) ^a	t \leq 10 sec	R_{thJA}	34	40	$^\circ\text{C/W}$
	Steady State		70	80	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	20	

Notes

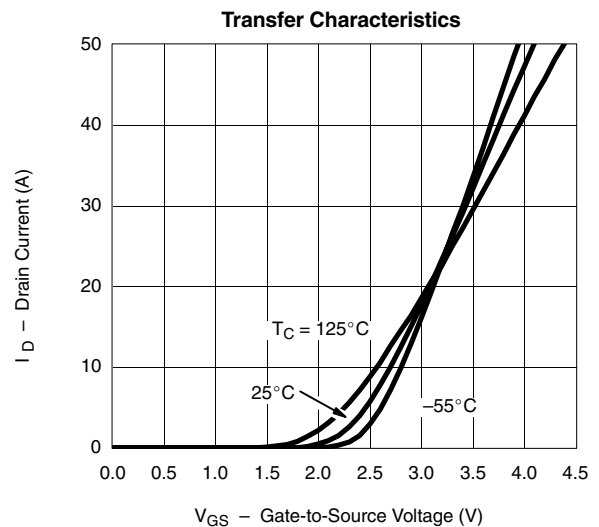
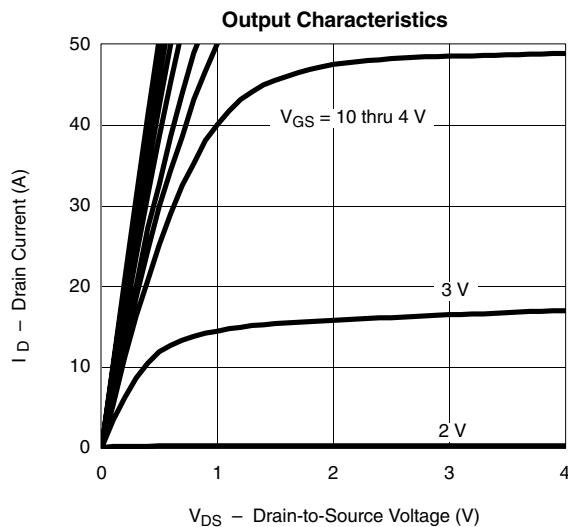
a. Surface Mounted on 1" x 1" FR4 Board.

MOSFET SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

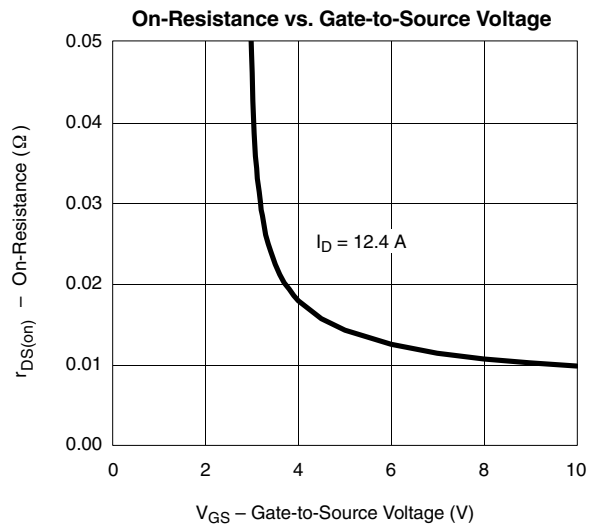
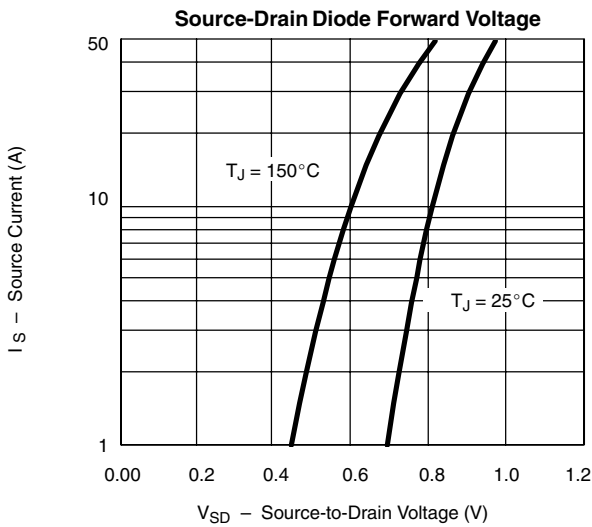
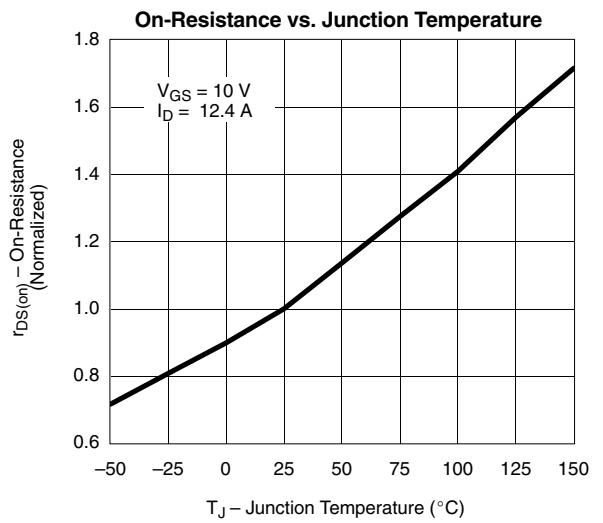
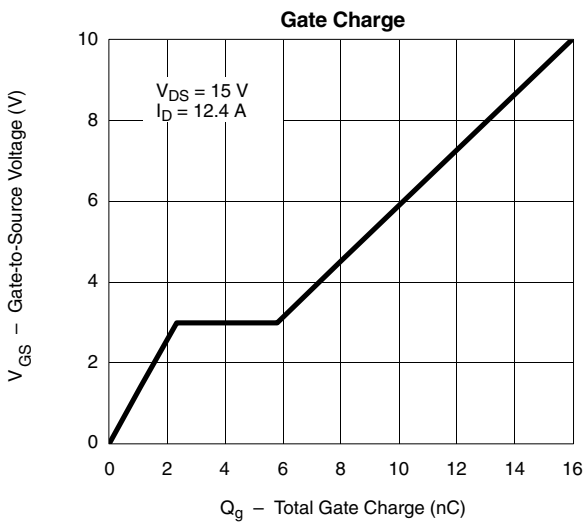
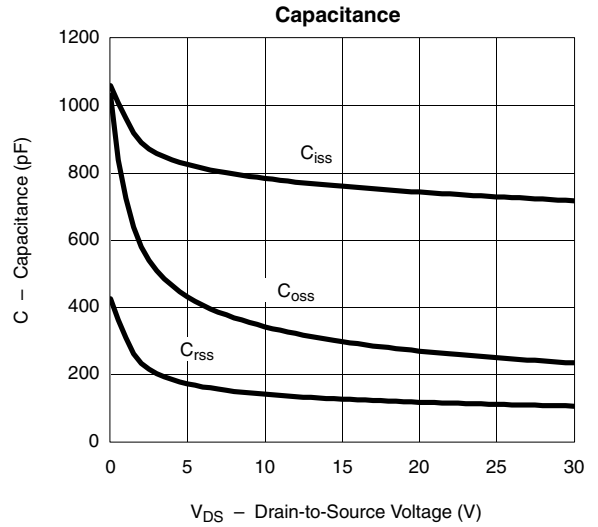
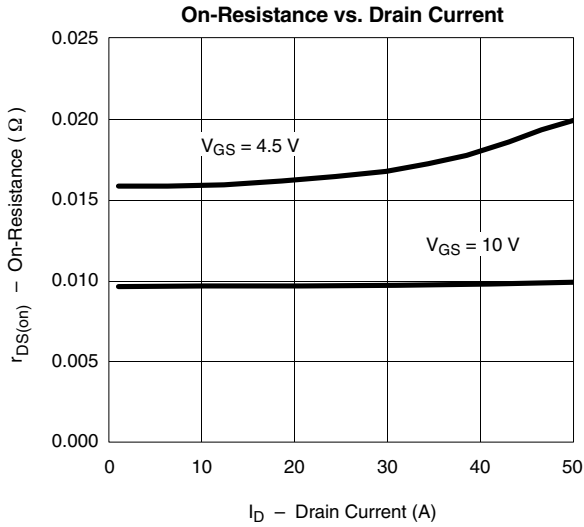
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	0.80			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 70^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5 \text{ V}, V_{GS} = 10 \text{ V}$	50			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10 \text{ V}, I_D = 12.4 \text{ A}$		0.010	0.012	Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 9.6 \text{ A}$		0.016	0.020	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}, I_D = 12.4 \text{ A}$		27		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.75	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 5.0 \text{ V}, I_D = 12.4 \text{ A}$		8.7	10.5	nC
Gate-Source Charge	Q_{gs}			2.4		
Gate-Drain Charge	Q_{gd}			3.5		
Gate Resistance	R_g		0.5	1.1	1.9	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15 \text{ V}, R_L = 15 \Omega$ $I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 6 \Omega$		10	20	ns
Rise Time	t_r			11	20	
Turn-Off Delay Time	$t_{d(off)}$			24	50	
Fall Time	t_f			10	20	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.6 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$		50	75	nC
Reverse Recovery Charge	Q_{rr}			38		

Notes

- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

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